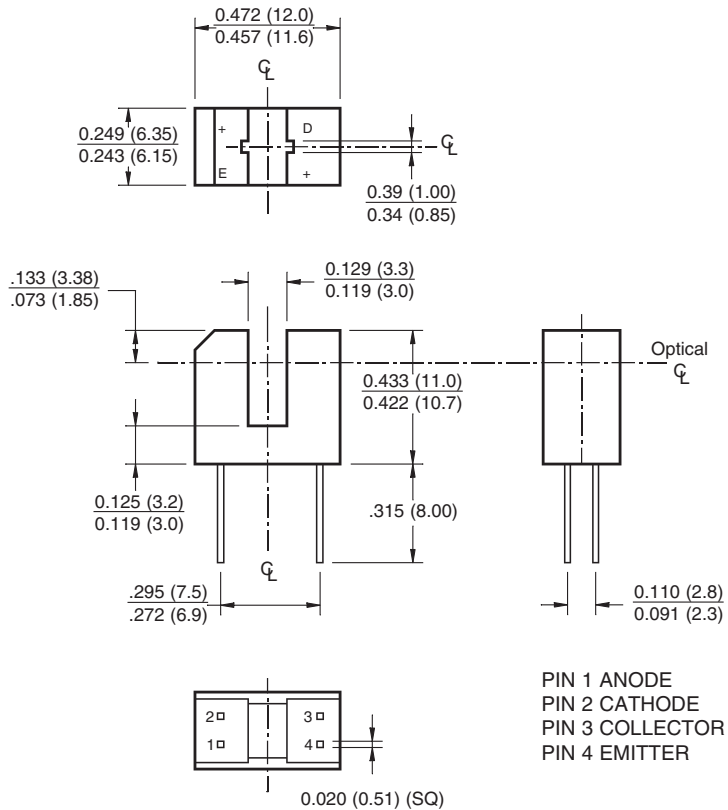


H22B1

H22B2

H22B3

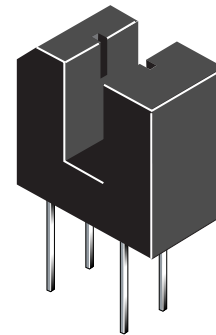
PACKAGE DIMENSIONS



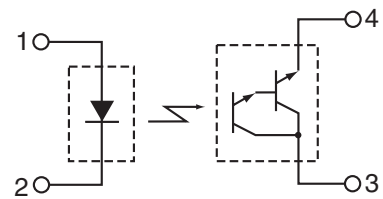
PIN 1 ANODE
PIN 2 CATHODE
PIN 3 COLLECTOR
PIN 4 EMITTER

NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010 (.25)$ on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The H22B1, H22B2 and H22B3 consist of a gallium arsenide infrared emitting diode coupled with a silicon photodarlington in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.

FEATURES

- Opaque housing
- Low cost
- .035" apertures
- High $I_{C(ON)}$

H22B1

H22B2

H22B3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Rating | Unit |
|---|-------------|----------------|------------------|
| Operating Temperature | T_{OPR} | -55 to +100 | $^\circ\text{C}$ |
| Storage Temperature | T_{STG} | -55 to +100 | $^\circ\text{C}$ |
| Soldering Temperature (Iron) ^(2,3 and 4) | T_{SOL-I} | 240 for 5 sec | $^\circ\text{C}$ |
| Soldering Temperature (Flow) ^(2 and 3) | T_{SOL-F} | 260 for 10 sec | $^\circ\text{C}$ |
| INPUT (EMITTER) | | | |
| Continuous Forward Current | I_F | 50 | mA |
| Reverse Voltage | V_R | 6 | V |
| Power Dissipation ⁽¹⁾ | P_D | 100 | mW |
| OUTPUT (SENSOR) | | | |
| Collector to Emitter Voltage | V_{CEO} | 30 | V |
| Emitter to Collector Voltage | V_{ECO} | 6 | V |
| Collector Current | I_C | 40 | mA |
| Power Dissipation ($T_C = 25^\circ\text{C}$) ⁽¹⁾ | P_D | 150 | mW |

NOTES:

1. Derate power dissipation linearly 1.67 mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6 mm) minimum from housing.

H22B1

H22B2

H22B3

ELECTRICAL/OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

| PARAMETER | TEST CONDITIONS | SYMBOL | DEVICES | MIN | TYP | MAX | UNITS |
|--------------------------------|--|---------------|---------|-----|-----|-----|---------------|
| INPUT (EMITTER) | | | | | | | |
| Forward Voltage | $I_F = 60 \text{ mA}$ | V_F | All | — | — | 1.7 | V |
| Reverse Breakdown Voltage | $I_R = 10 \mu\text{A}$ | V_R | All | 6.0 | — | — | V |
| Reverse Leakage Current | $V_R = 3 \text{ V}$ | I_R | All | — | — | 1.0 | μA |
| OUTPUT (SENSOR) | | | | | | | |
| Emitter to Collector Breakdown | $I_F = 100 \mu\text{A}, E_e = 0$ | BV_{ECO} | All | 7.0 | — | — | V |
| Collector to Emitter Breakdown | $I_C = 1 \text{ mA}, E_e = 0$ | BV_{CEO} | All | 30 | — | — | V |
| Collector to Emitter Leakage | $V_{CE} = 25 \text{ V}, E_e = 0$ | I_{CEO} | All | — | — | 100 | nA |
| COUPLED | | | | | | | |
| On-State Collector Current | $I_F = 2 \text{ mA}, V_{CE} = 1.5 \text{ V}$ | $I_{C(ON)}$ | H22B1 | 0.5 | — | — | mA |
| | | | H22B2 | 1.0 | — | — | |
| | | | H22B3 | 2.0 | — | — | |
| | $I_F = 5 \text{ mA}, V_{CE} = 1.5 \text{ V}$ | | H22B1 | 2.5 | — | — | |
| | | | H22B2 | 5.0 | — | — | |
| | | | H22B3 | 10 | — | — | |
| | $I_F = 10 \text{ mA}, V_{CE} = 1.5 \text{ V}$ | | H22B1 | 7.5 | — | — | |
| | | | H22B2 | 14 | — | — | |
| | | | H22B3 | 25 | — | — | |
| Saturation Voltage | $I_F = 10 \text{ mA}, I_C = 1.8 \text{ mA}$ | $V_{CE(SAT)}$ | All | — | — | 1.0 | V |
| | $I_F = 60 \text{ mA}, I_C = 50 \text{ mA}$ | | H22B1/2 | — | — | 1.5 | V |
| Turn-On Time | $I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$ | t_{on} | All | — | 45 | — | μs |
| | $I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75\Omega$ | | All | — | 7 | — | |
| Turn-Off Time | $I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$ | t_{off} | All | — | 250 | — | μs |
| | $I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75\Omega$ | | All | — | 45 | — | |

H22B1

H22B2

H22B3

Figure 1. Output Current vs. Input Current

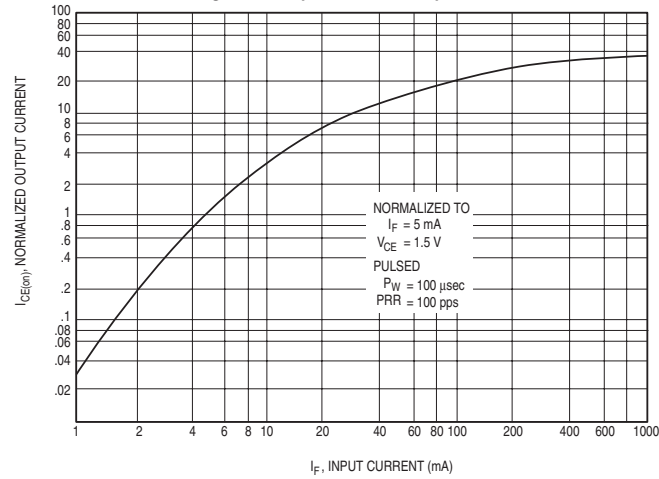


Figure 2. Output Current vs. Temperature

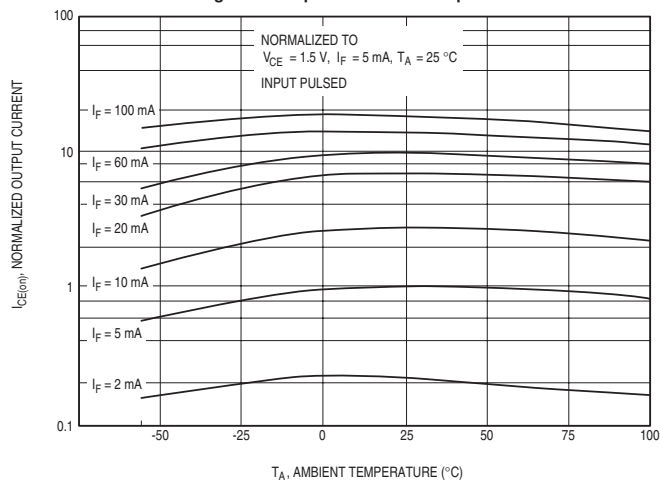
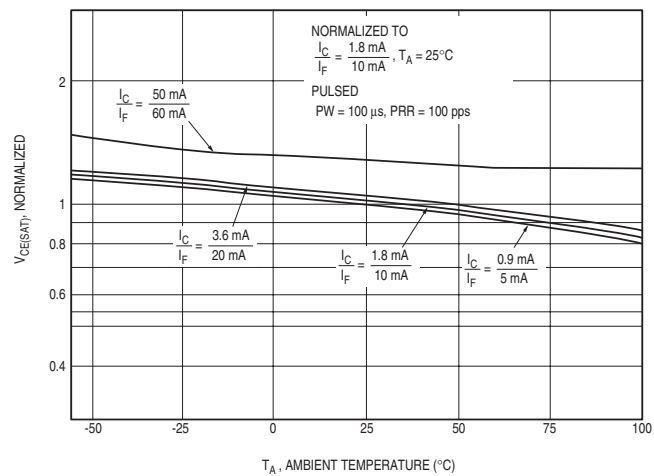


Figure 3. $V_{CE(SAT)}$ vs. Temperature



H22B1

H22B2

H22B3

Figure 4. Leakage Current vs. Temperature

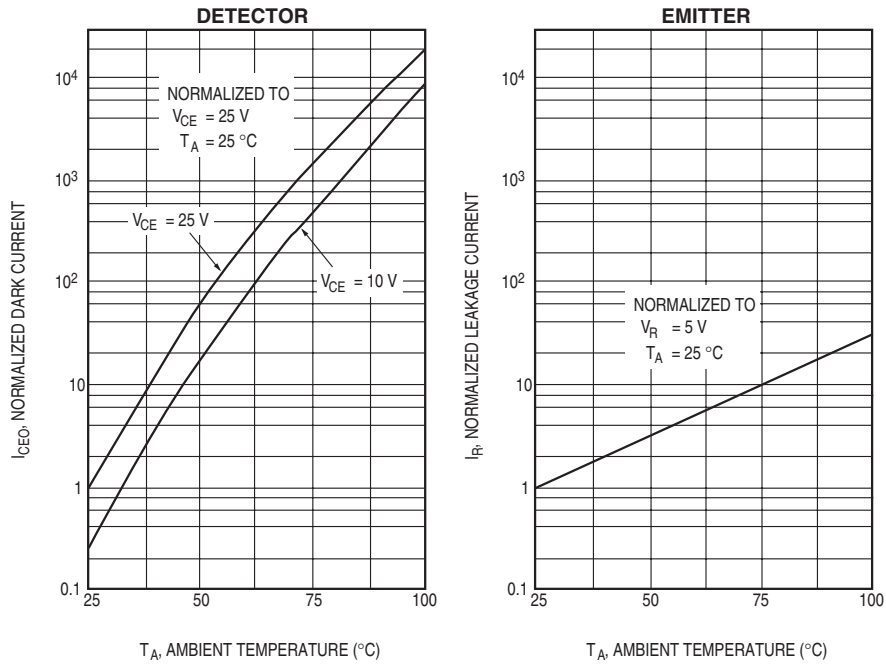


Figure 5. Switching Speed vs. R_L

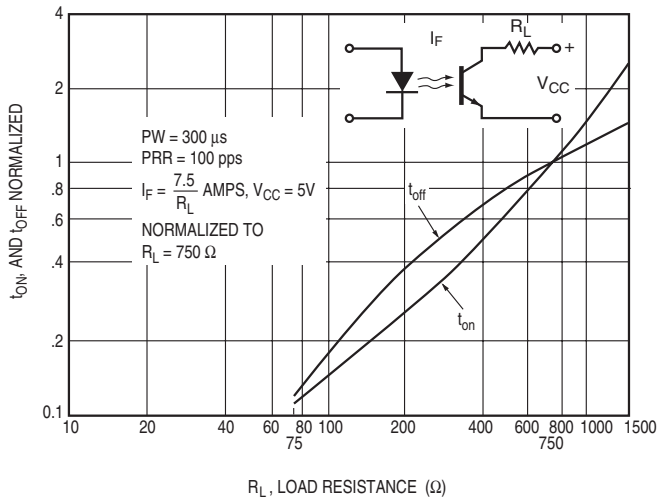
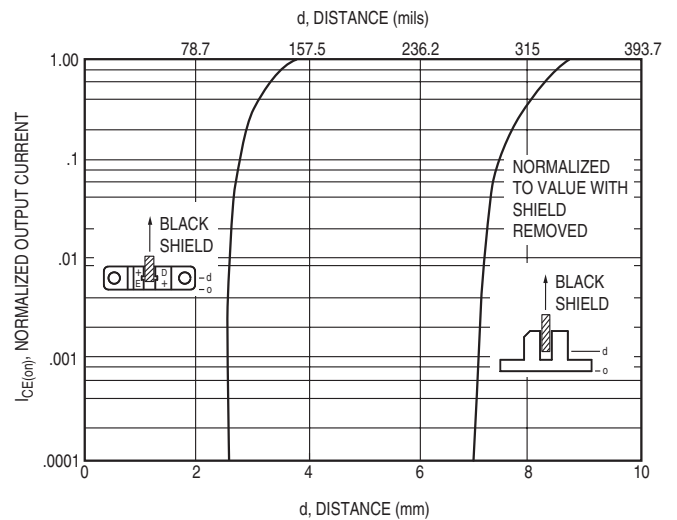


Figure 6. Output Current vs. Distance



H22B1

H22B2

H22B3

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